

AMENDMENTS TO THE CLAIMS

Claims 1-12. Cancelled

13. (Currently Amended) A semiconductor device comprising:

a layer that is transparent to light having a wavelength of approximately 248 nm; and

a first anti-reflective coating extending substantially entirely beneath the transparent layer.

14. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

15. (Original) The semiconductor device of claim 13 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

16. (Original) The semiconductor device of claim 13 wherein the transparent layer includes an oxide.

17. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising an organic polymer.

18. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

19. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

20. (Original) The semiconductor device of claim 13 further including:
a second anti-reflective coating extending over the transparent layer.

21. (Currently Amended) A semiconductor device comprising:
a layer that is transparent to light having a wavelength of approximately 365 nm; and
a first anti-reflective coating extending substantially entirely beneath the transparent layer.

22. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

23. (Original) The semiconductor device of claim 21 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

24. (Original) The semiconductor device of claim 21 wherein the transparent layer includes an oxide.

25. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

26. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

27. (Original) The semiconductor device of claim 21 further including:
a second anti-reflective coating extending over the transparent layer.

28. (Currently Amended) A semiconductor device comprising:
a layer that is transparent to light having a wavelength of approximately 193 nm; and
a first anti-reflective coating extending substantially entirely beneath the transparent layer.

29. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

30. (Original) The semiconductor device of claim 28 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

31. (Original) The semiconductor device of claim 28 wherein the transparent layer includes an oxide.

32. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

33. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

34. (Original) The semiconductor device of claim 28 further including:

a second anti-reflective coating extending over the transparent layer.

35. (New) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

36. (New) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

37. (New) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising an organic polymer.

38. (New) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

39. (New) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

40. (New) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising an organic polymer.

41. (New) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

42. (New) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

43. (New) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising an organic polymer.